



STGP3NB60K - STGD3NB60K

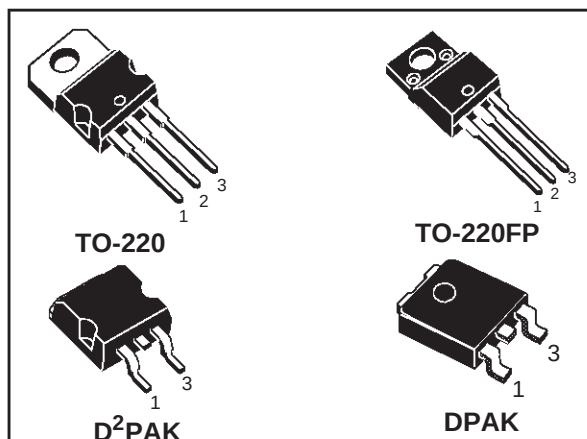
STGP3NB60KD-STGP3NB60KDFP-STGB3NB60KD

N-CHANNEL 3A - 600V - TO-220/DPAK/D²PAK

PowerMESH™ IGBT

TYPE	V _{CES}	V _{CE(sat)} (Typ) @125°C	I _C @125°C
STGP3NB60K	600 V	< 2 V	3 A
STGD3NB60K	600 V	< 2 V	3 A
STGP3NB60KD	600 V	< 2 V	3 A
STGP3NB60KDFP	600 V	< 2 V	3 A
STGB3NB60KD	600 V	< 2 V	3 A

- HIGH INPUT IMPEDANCE (VOLTAGE DRIVEN)
- LOW ON-VOLTAGE DROP (V_{cesat})
- LOW GATE CHARGE
- HIGH CURRENT CAPABILITY
- OFF LOSSES INCLUDE TAIL CURRENT
- HIGH FREQUENCY OPERATION
- SHORT CIRCUIT RATED

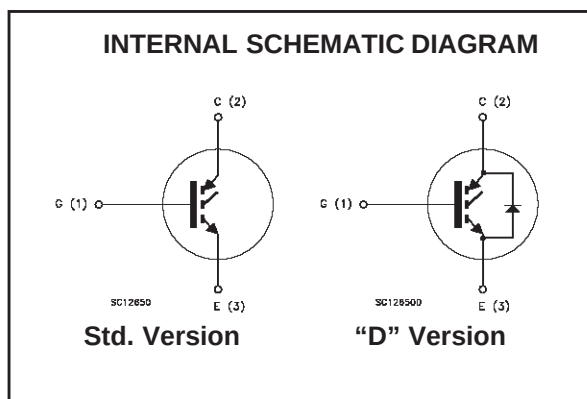


DESCRIPTION

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances. The suffix "K" identifies a family optimized for high frequency motor control applications with short circuit withstand capability.

APPLICATIONS

- HIGH FREQUENCY MOTOR CONTROLS
- SMPS AND PFC IN BOTH HARD SWITCHING AND RESONANT TOPOLOGIES



ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STGP3NB60K	GP3NB60K	TO-220	TUBE
STGD3NB60KT4	GD3NB60K	DPAK	TAPE & REEL
STGP3NB60KD	GP3NB60KD	TO-220	TUBE
STGP3NB60KDFP	GP3NB60KDFP	TO-220FP	TUBE
STGB3NB60KDT4	GB3NB60KD	D ² PAK	TAPE & REEL

STGP3NB60K/STGD3NB60K/STGP3NB60KD/STGP3NB60KDFP/STGB3NB60KD**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value			Unit
		TO-220 D ² PAK	TO-220FP	DPAK	
V _{CES}	Collector-Emitter Voltage (V _{GS} = 0)	600			V
V _{ECR}	Emitter-Collector Voltage	20			V
V _{GE}	Gate-Emitter Voltage	±20			V
I _C	Collector Current (continuous) at T _C = 25°C	6	6	6	A
I _C	Collector Current (continuous) at T _C = 100°C	3	3	3	A
I _{CM} ⁽¹⁾	Collector Current (pulsed)	24	24	24	A
I _f (1)	Forward Current	3			A
I _{fm} (1)	Forward Current Pulsed	24			A
P _{TOT}	Total Dissipation at T _C = 25°C	68	25	60	W
	Derating Factor	0.75			W/°C
V _{ISO}	Insulation Withstand Voltage A.C.	--	2500	--	V
T _{stg}	Storage Temperature	– 55 to 150 150			°C
T _j	Max. Operating Junction Temperature				

(1) Pulse width limited by safe operating area

(1) For "D" version only

THERMAL DATA

		TO-220 D ² PAK	TO-220FP	DPAK	
Rthj-case	Thermal Resistance Junction-case Max	1.8	5	2.1	°C/W
Rthj-amb	Thermal Resistance Junction-ambient Max	62.5		100	°C/W
Rthc-h	Thermal Resistance Case-heatsink Typ	0.5			°C/W

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C UNLESS OTHERWISE SPECIFIED)**MAIN PARAMETERS**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{BR(CES)}	Collector-Emitter Breakdown Voltage	I _C = 250 μA, V _{GE} = 0	600			V
I _{CES}	Collector cut-off (V _{GE} = 0)	V _{CE} = Max Rating, T _C = 25 °C V _{CE} = Max Rating, T _C = 125 °C			50 500	μA μA
I _{GES}	Gate-Emitter Leakage Current (V _{CE} = 0)	V _{GE} = ±20V, V _{CE} = 0			±100	nA
V _{GE(th)}	Gate Threshold Voltage	V _{CE} = V _{GE} , I _C = 250μA	5		7	V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	V _{GE} = 15V, I _C = 3 A V _{GE} = 15V, I _C = 3 A, T _j = 125°C		2.3 1.9	2.8	V V

SWITCHING PARAMETERS

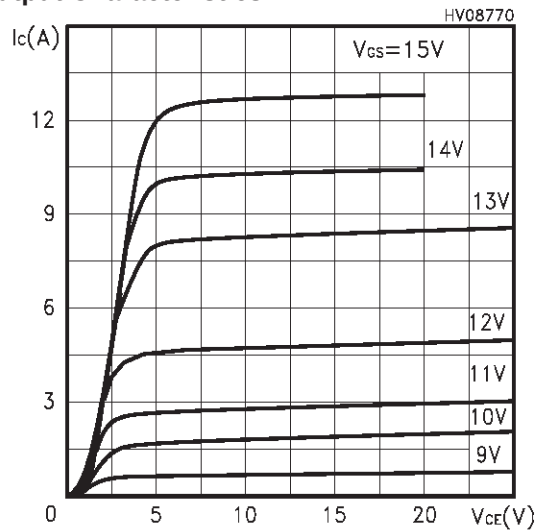
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs}	Forward Transconductance	$V_{CE} = 25V, I_C = 3 A$		2.4		S
C_{ies} C_{oes} C_{res}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{CE} = 25V, f = 1 MHz, V_{GE} = 0$		218 33 5.8		pF pF pF
Q_g Q_{ge} Q_{gc}	Total Gate Charge Gate-Emitter Charge Gate-Collector Charge	$V_{CE} = 480V, I_C = 3 A,$ $V_{GE} = 15V$		14 3.3 7.5	18	nC nC nC
t_{scw}	Short Circuit Withstand Time	$V_{ce} = 0.5 V_{BR(CES)}, V_{GE}=15V,$ $T_j = 125^{\circ}C, R_G = 10 \Omega$	10			μs
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{CC} = 480 V, I_C = 3 A$ $R_G = 10\Omega, V_{GE} = 15 V$		14 5		ns ns
$(di/dt)_{on}$ E_{on}	Turn-on Current Slope Turn-on Switching Losses	$V_{CC}= 480 V, I_C = 3 A R_G=10\Omega$ $V_{GE} = 15 V, T_j = 125^{\circ}C$		520 30		A/ μs μJ
t_c $t_r(V_{off})$ $t_{d(off)}$ t_f $E_{off(**)}$ E_{ts}	Cross-over Time Off Voltage Rise Time Delay Time Fall Time Turn-off Switching Loss Total Switching Loss	$V_{CC} = 480 V, I_C = 3 A,$ $R_{GE} = 10 \Omega, V_{GE} = 15 V$ $T_j = 25^{\circ}C$		122 26.5 33 100 58 85		ns ns ns ns μJ μJ
t_c $t_r(V_{off})$ $t_{d(off)}$ t_f $E_{off(**)}$ E_{ts}	Cross-over Time Off Voltage Rise Time Delay Time Fall Time Turn-off Switching Loss Total Switching Loss	$V_{CC} = 480 V, I_C = 3 A,$ $R_{GE} = 10 \Omega, V_{GE} = 15 V$ $T_j = 125^{\circ}C$		210 66 100 120 165 195		ns ns ns ns μJ μJ

COLLECTOR-EMITTER DIODE ("D" VERSION)

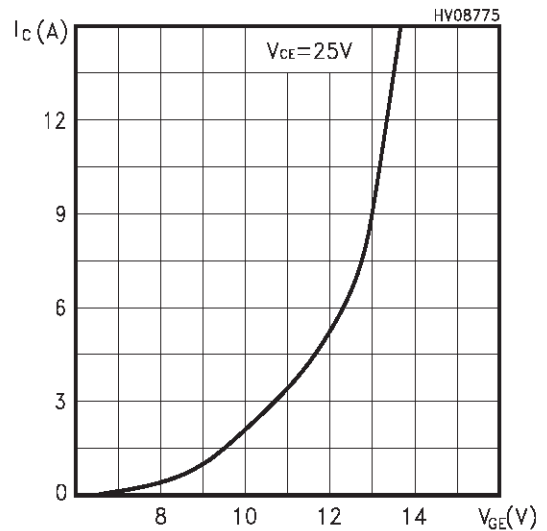
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_f	Forward On-Voltage	$I_f = 1.5 A$ $I_f = 1.5 A, T_j = 125^{\circ}C$		1.31 0.95	1.8	V V
t_{rr} Q_{rr} I_{rrm}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_f = 3 A, V_R = 35 V,$ $T_j = 125^{\circ}C, di/dt = 100A/\mu s$		45 70 2.7		ns nC A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.
2. Pulse width limited by max. junction temperature.
(**) Losses include Also the Tail (Jedec Standardization)

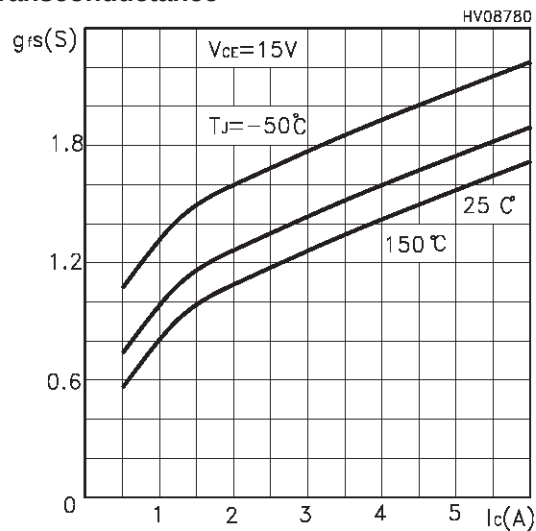
Output Characteristics



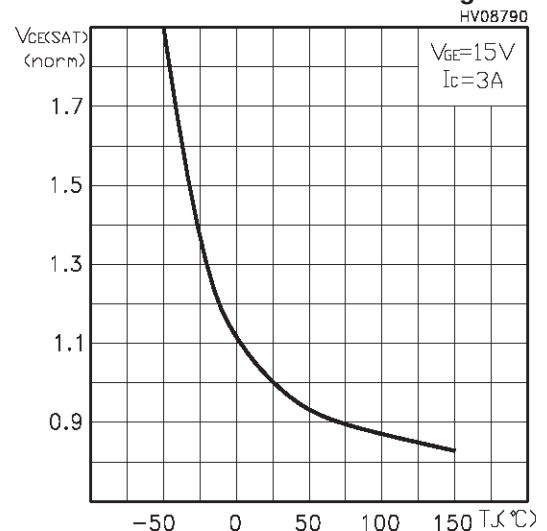
Transfer Characteristics



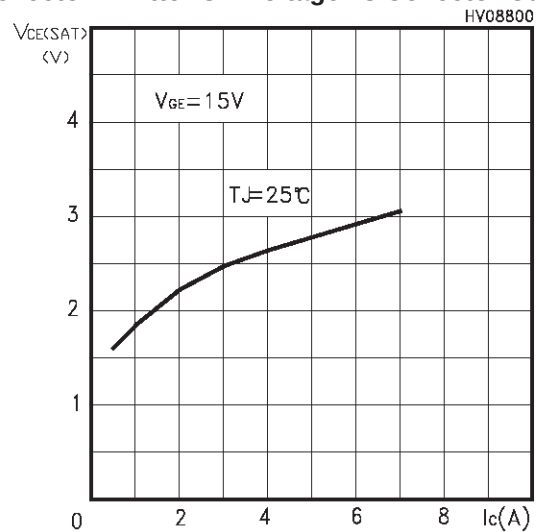
Transconductance



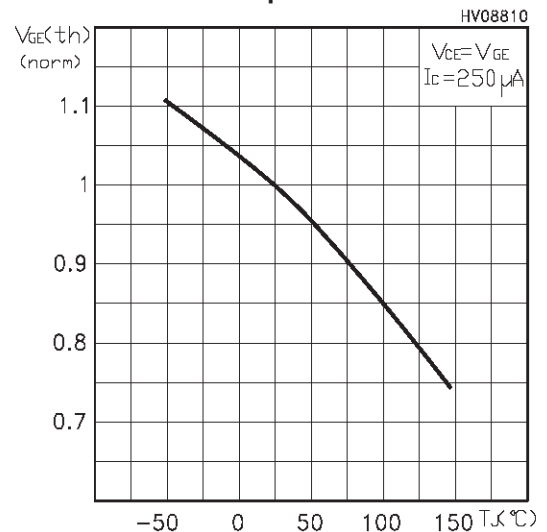
Normalized Collector-Emitter On Voltage vs Temp.



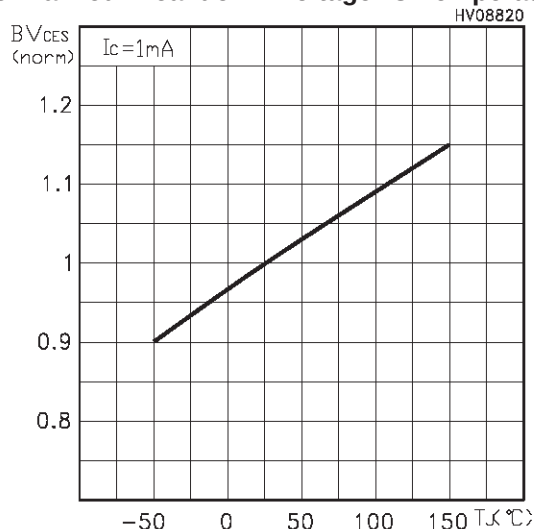
Collector-Emitter On Voltage vs Collector Current



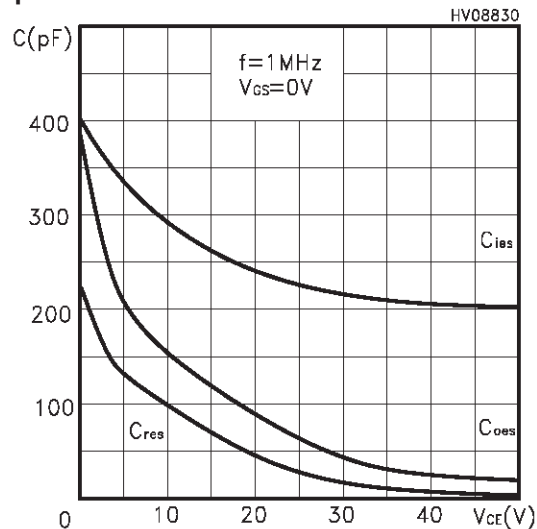
Gate Threshold vs Temperature



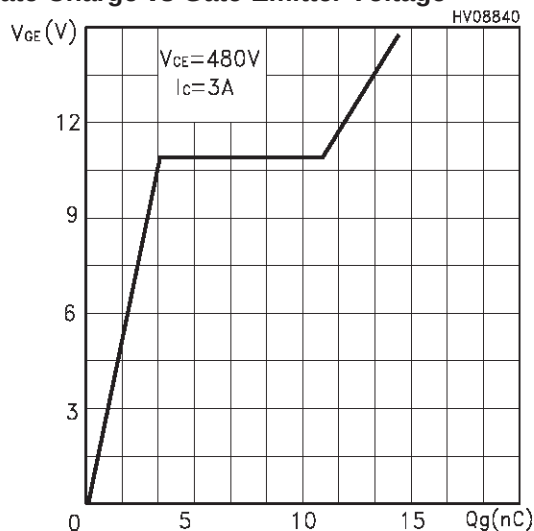
Normalized Breakdown Voltage vs Temperature



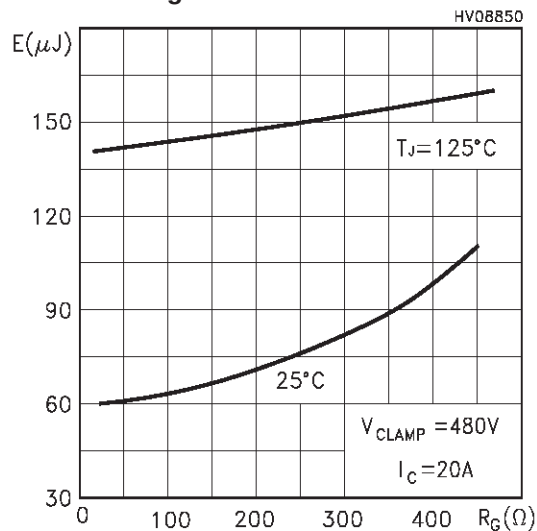
Capacitance Variations



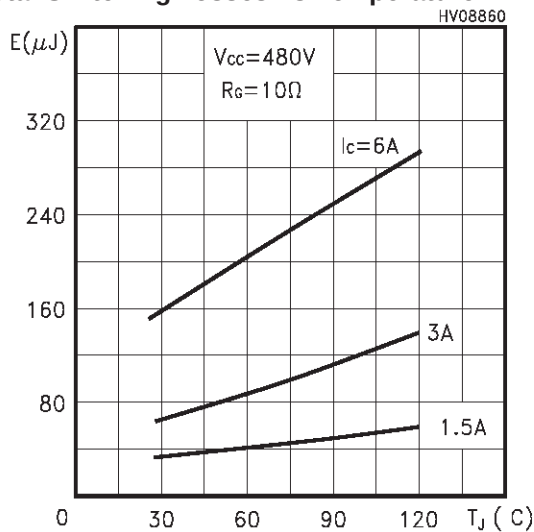
Gate Charge vs Gate-Emmitter Voltage



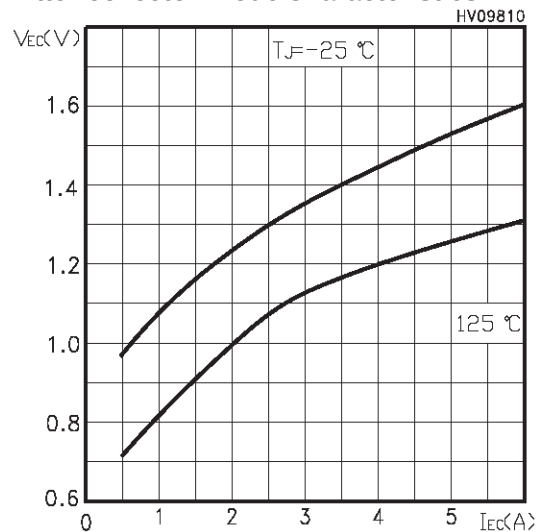
Total Switching Losses vs Gate Resistance



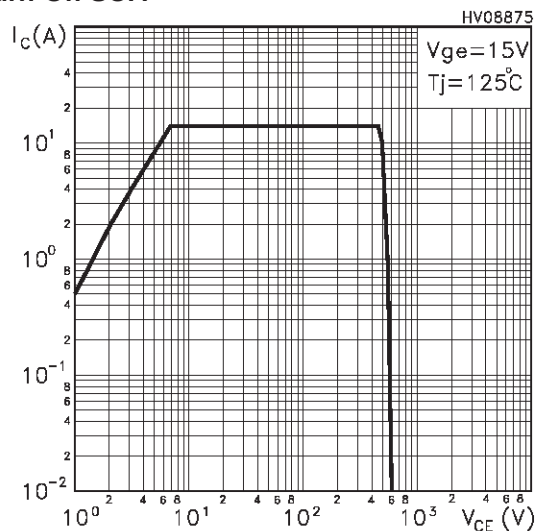
Total Switching Losses vs Temperature



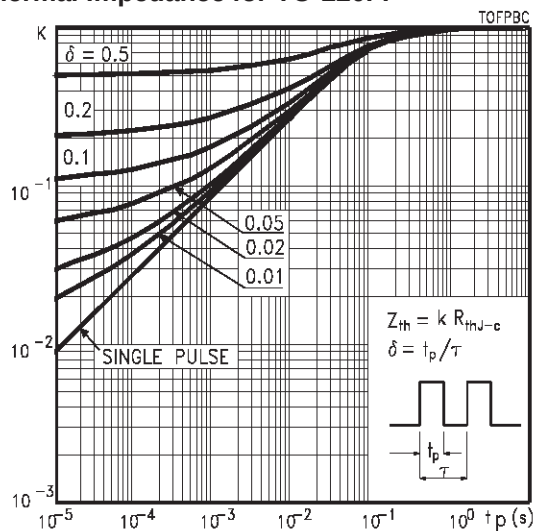
Emitter-collector Diode Characteristics



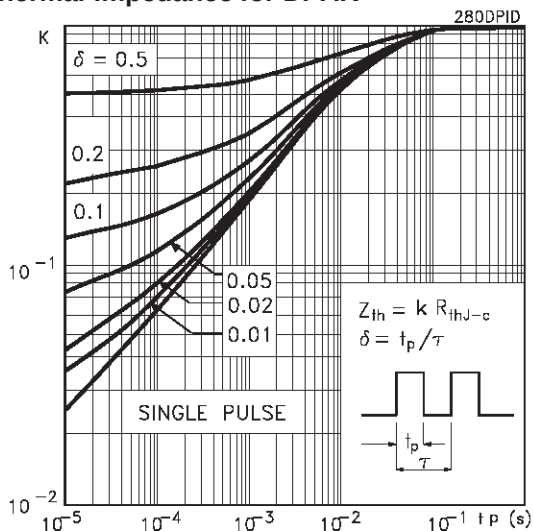
Turn-Off SOA



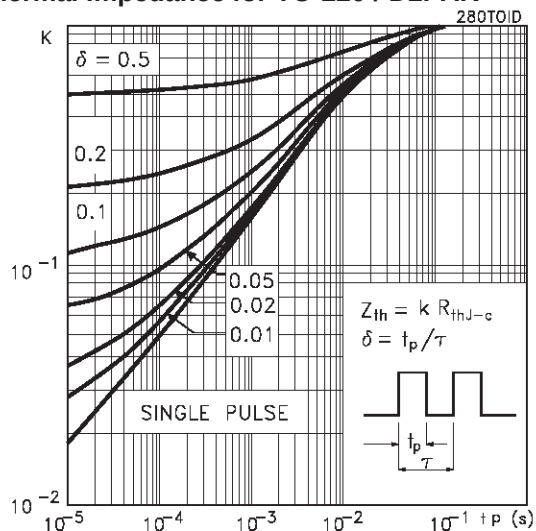
Thermal Impedance for TO-220FP



Thermal Impedance for DPAK

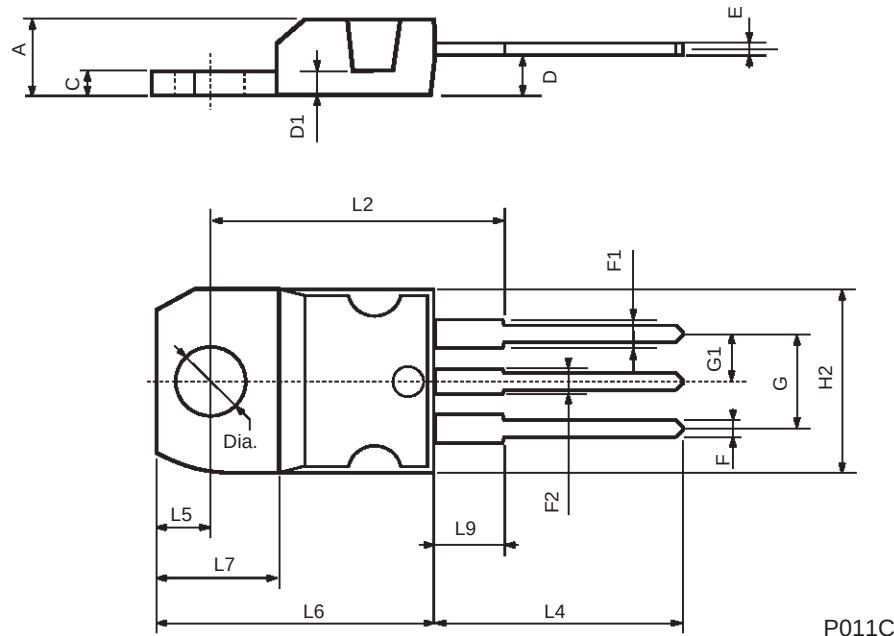


Thermal Impedance for TO-220 / D2PAK



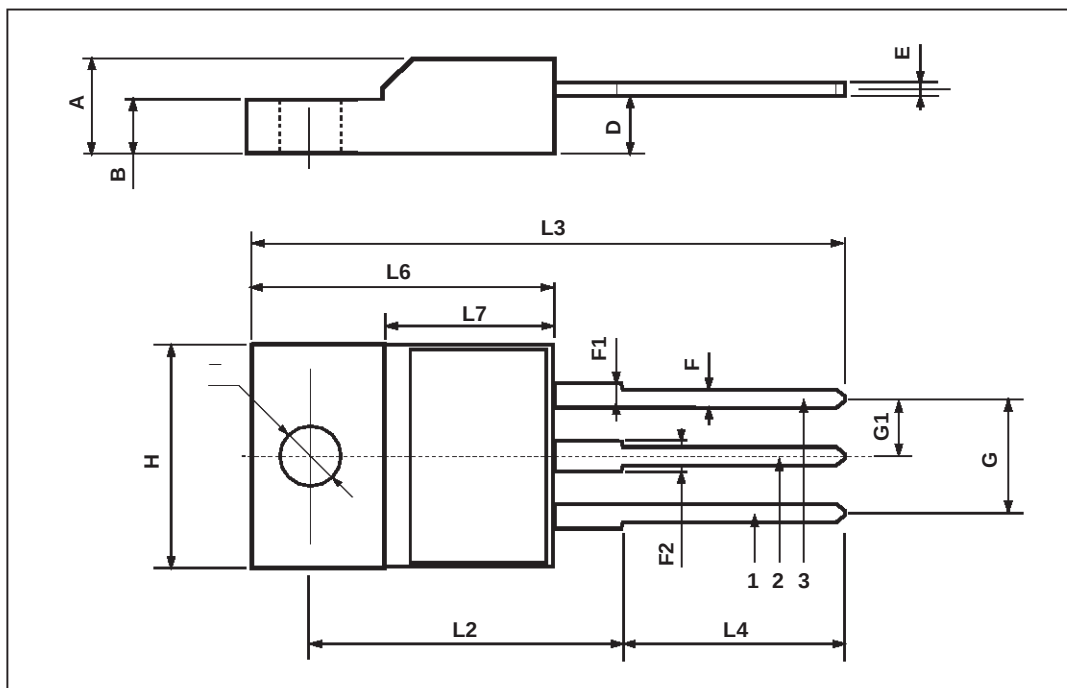
TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.051
D	2.40		2.72	0.094		0.107
D1		1.27			0.050	
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.203
G1	2.4		2.7	0.094		0.106
H2	10.0		10.40	0.393		0.409
L2		16.4			0.645	
L4	13.0		14.0	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.2		6.6	0.244		0.260
L9	3.5		3.93	0.137		0.154
DIA.	3.75		3.85	0.147		0.151



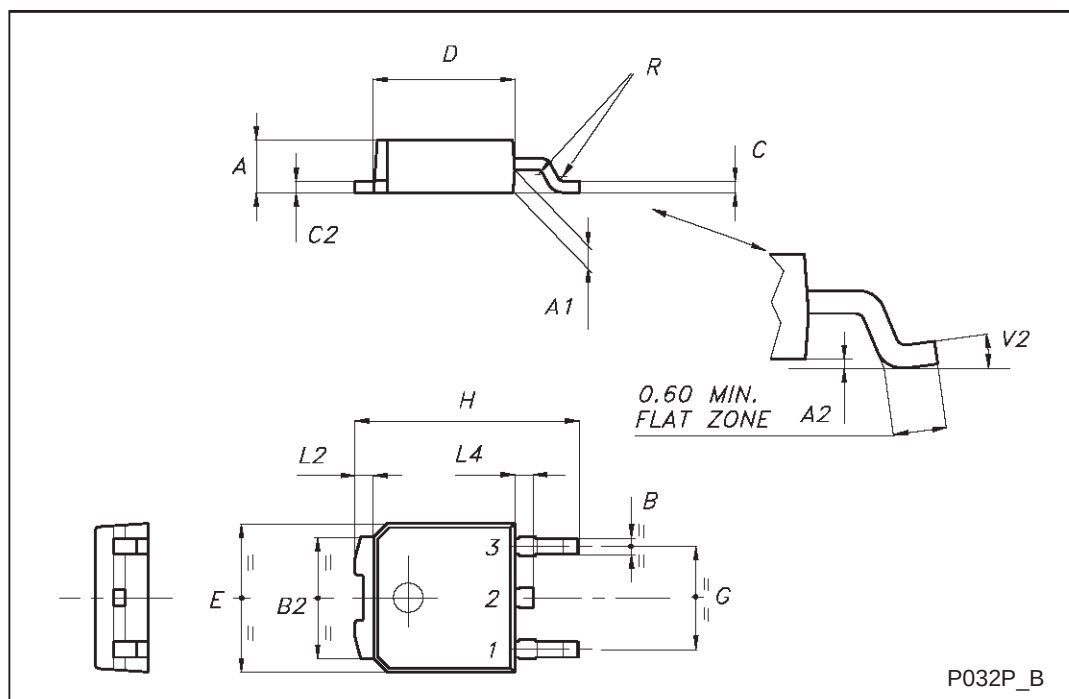
TO-220FP MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	0.385		0.417
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



TO-252 (DPAK) MECHANICAL DATA

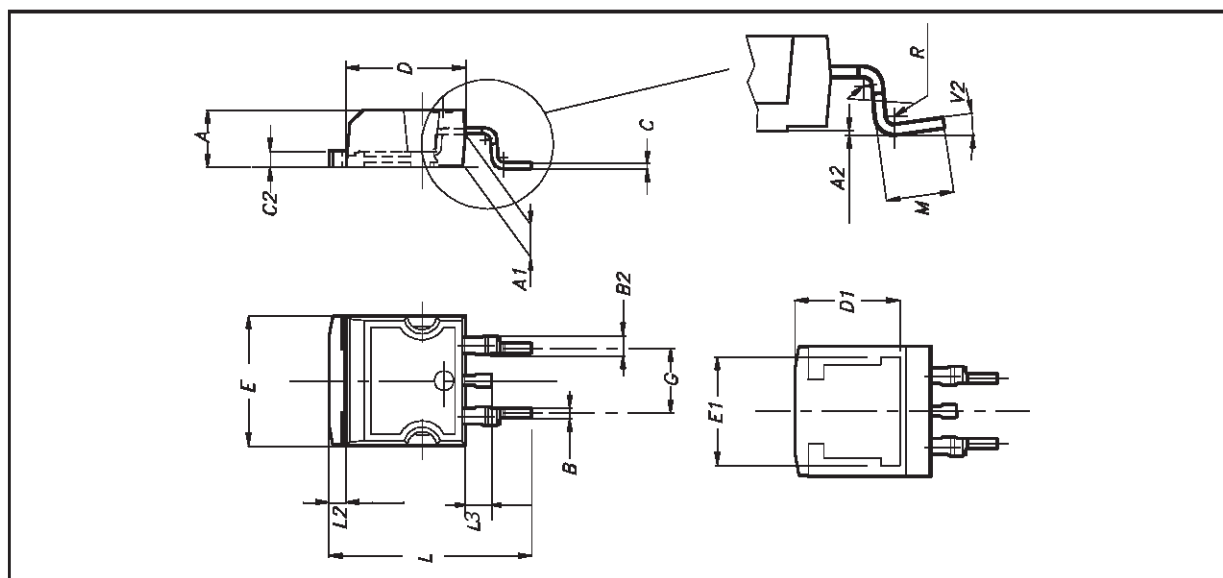
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°



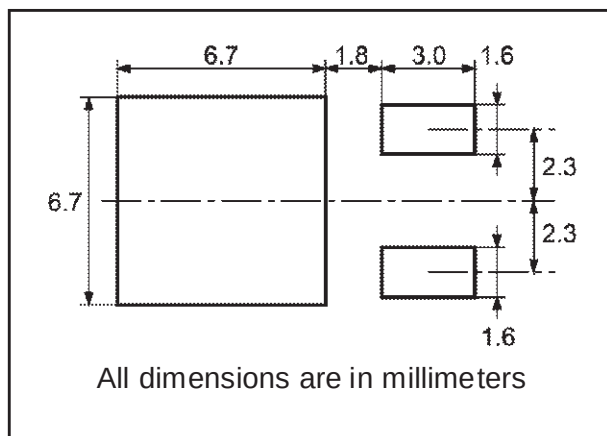
P032P_B

D²PAK MECHANICAL DATA

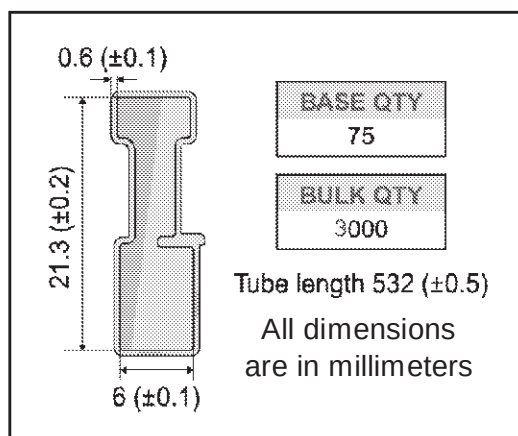
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		8°			



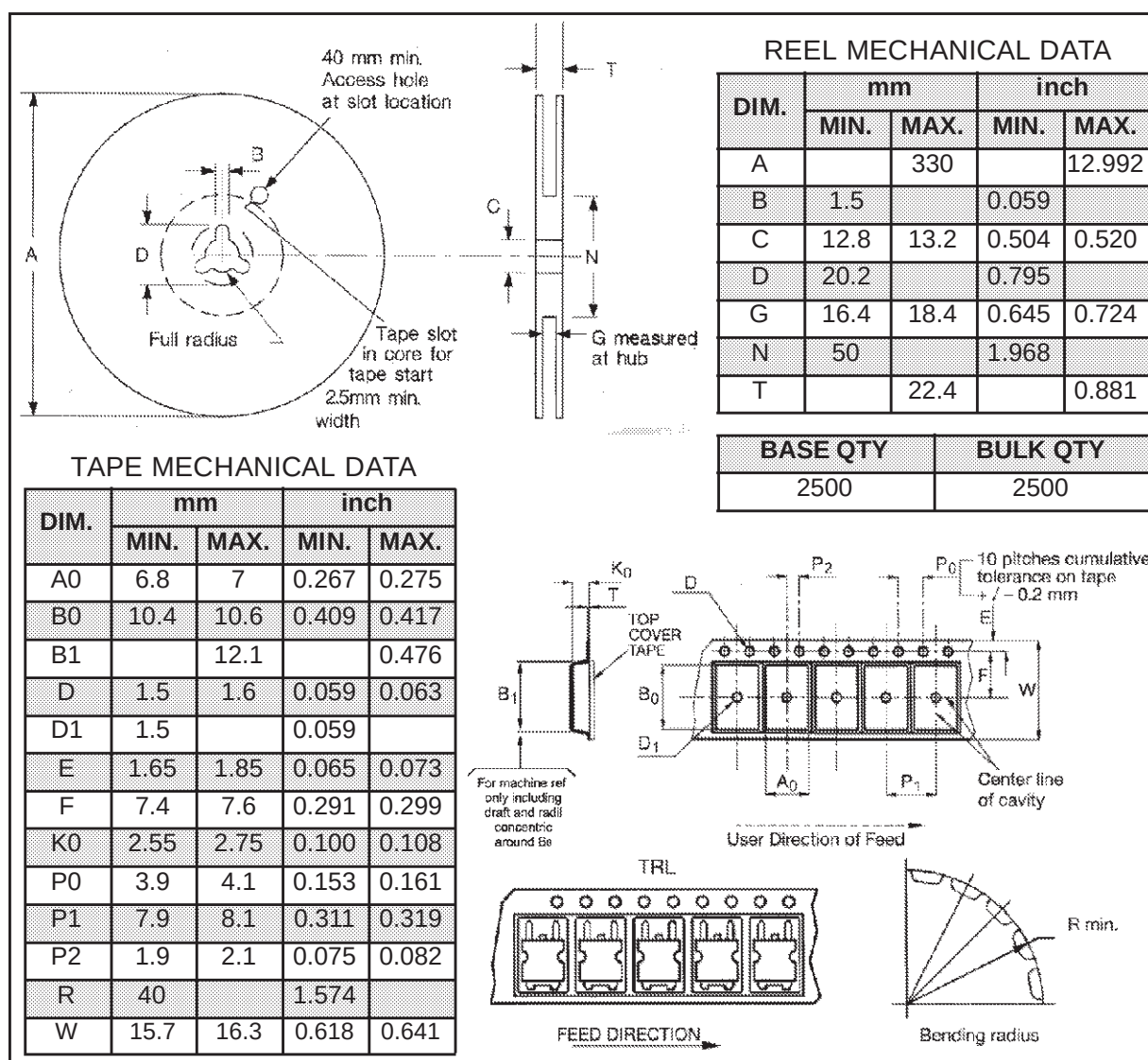
DPAK FOOTPRINT



TUBE SHIPMENT (no suffix)*

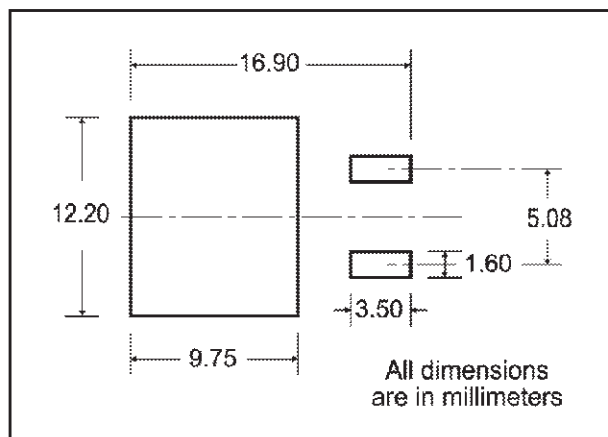


TAPE AND REEL SHIPMENT (suffix "T4")*

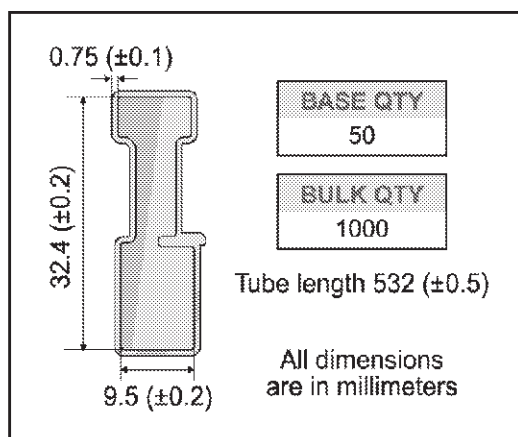


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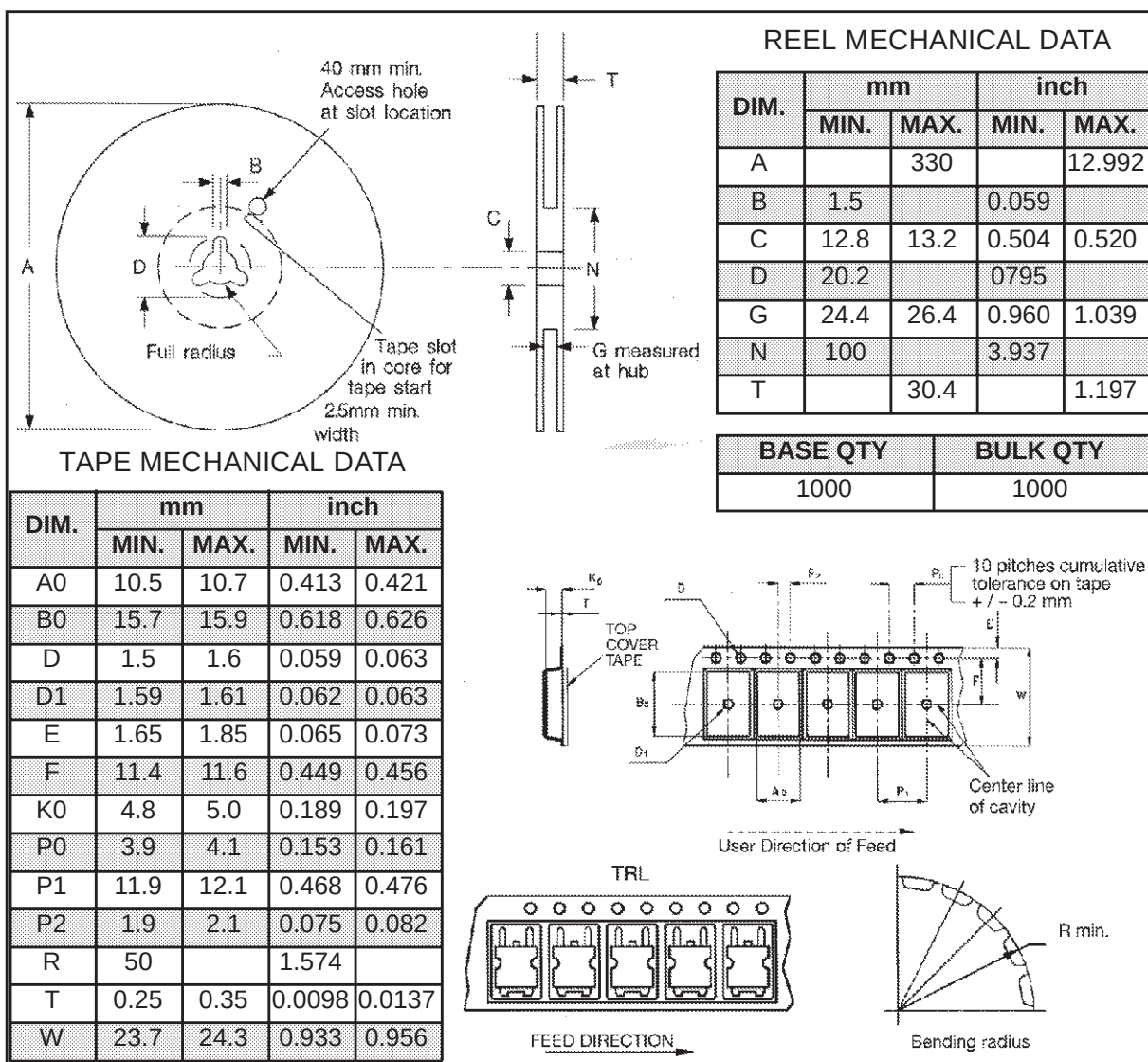
D²PAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*



* on sales

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